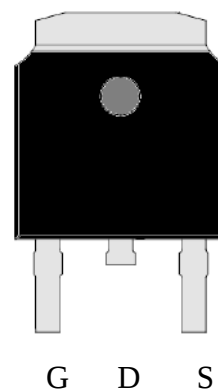


P-Channel Enhancement Mode Power MOSFET

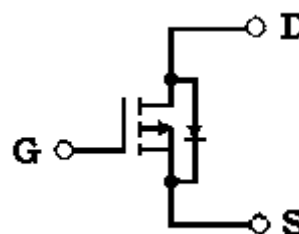
Features:

- Single Drive Requirement
- Low On-resistance
- Fast switching Characteristic
- Pb-free lead plating and halogen-free package

TO-252(DPAK)



BV_{DSS}	-60V
I_D @ V_{GS}=-10V, T_C=25°C	-56A
I_D @ V_{GS}=-10V, T_A=25°C	-10A
R_{DS(ON)}@V_{GS}=-10V, I_D=-20A	10.6mΩ(typ)



G : Gate
D : Drain
S : Source

Ordering Information

Device	Package	Shipping
KJE010P06	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current @V _{GS} =-10V, T _C =25°C	I _D	-56	A
Continuous Drain Current @V _{GS} =-10V, T _C =100°C		-35.5	
Continuous Drain Current @V _{GS} =-10V, T _A =25°C		-10	
Continuous Drain Current @V _{GS} =-10V, T _A =100°C		-6.3	
Pulsed Drain Current	I _{DM}	-224 *1	
Single Pulse Avalanche Current @ L=0.1mH	I _{AS}	-60	mJ
Single Pulse Avalanche Energy @ L=1mH, I _{AS} =-30A, V _{DD} =-25V	E _{AS}	450 *2	
Power Dissipation	P _D	T _C =25°C	W
		T _C =100°C	
		T _A =25°C	
		T _A =100°C	
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	1.6	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	50 *3	

Note : *1. Pulse width limited by safe operating area.

*2 . 100% tested by conditions of V_{DD}=-25V, L=0.1mH, V_{GS}=-10V, I_{AS}=-30A.

*3 . The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

*4 . The power dissipation P_D is more useful in setting the upper dissipation limit for cases where additional heatsinking is used. It is used to determined the current rating, when this rating falls below the package limit.

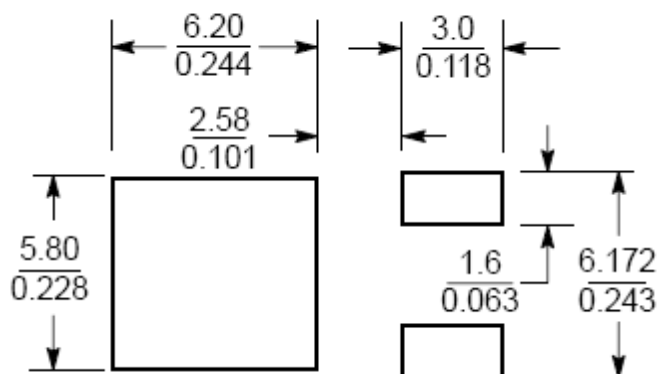
Characteristics (T_j=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-60	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-2	-	-4		V _{DS} = V _{GS} , I _D =-250μA
G _{FS}	-	26.4	-	S	V _{DS} = -10V, I _D =-20A
I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} = -48V, V _{GS} = 0V
	-	-	-25		V _{DS} = -48V, V _{GS} = 0V, T _j =70°C
*R _{DS(ON)}	-	10.6	14	mΩ	V _{GS} = -10V, I _D =-20A
Dynamic					
*Q _g	-	67	-	nC	I _D =-20A, V _{DS} =-48V, V _{GS} =-10V
*Q _{gs}	-	11.5	-		
*Q _{gd}	-	26	-		

*t _{d(ON)}	-	26.8	-	ns	V _{DS} =-30V, V _{GS} =-10V, R _G =1Ω, I _D =-20A
*t _r	-	27.8	-		
*t _{d(OFF)}	-	59.4	-		
*t _f	-	16.4	-		
C _{iss}	-	3124	-	pF	V _{GS} =0V, V _{DS} =-30V, f=1MHz
C _{oss}	-	353	-		
C _{rss}	-	205	-		
R _g	-	3.7	-	Ω	f=1MHz
Source-Drain Diode					
*I _S	-	-	-56	A	
*I _{SM}	-	-	-224		
*V _{SD}	-	-0.84	-1.2	V	I _S =-20A, V _{GS} =0V
*t _{rr}	-	23.4	-	ns	I _F =-20A, V _{GS} =0V, dI _F /dt=100A/μs
*Q _{rr}	-	20.8	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

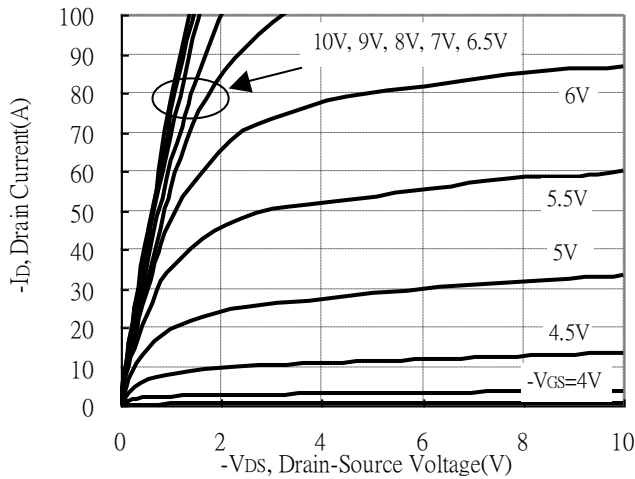
Recommended soldering footprint



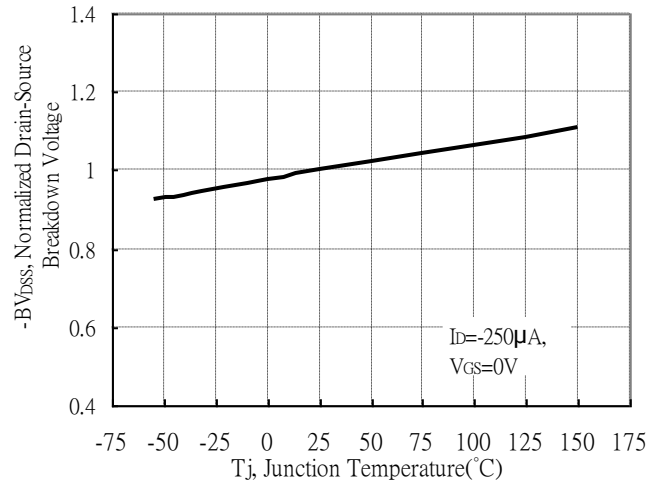
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

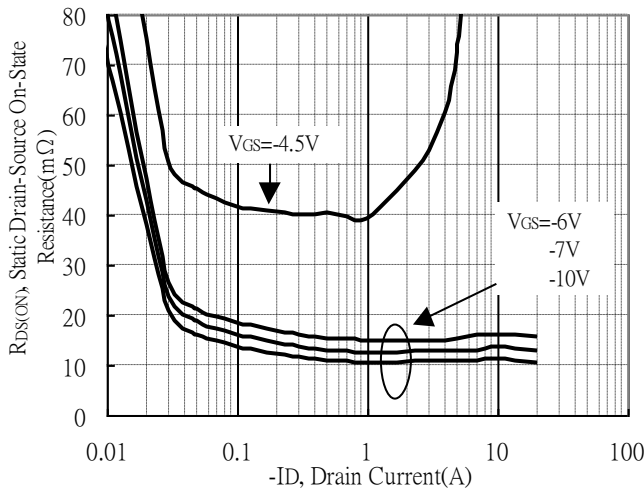
Typical Output Characteristics



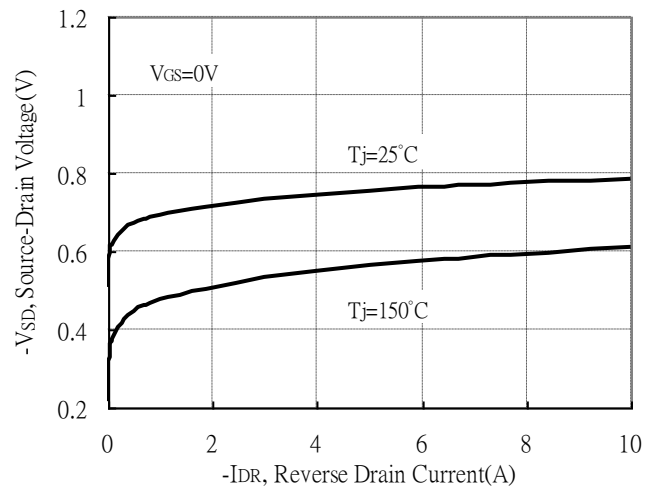
Breakdown Voltage vs Ambient Temperature



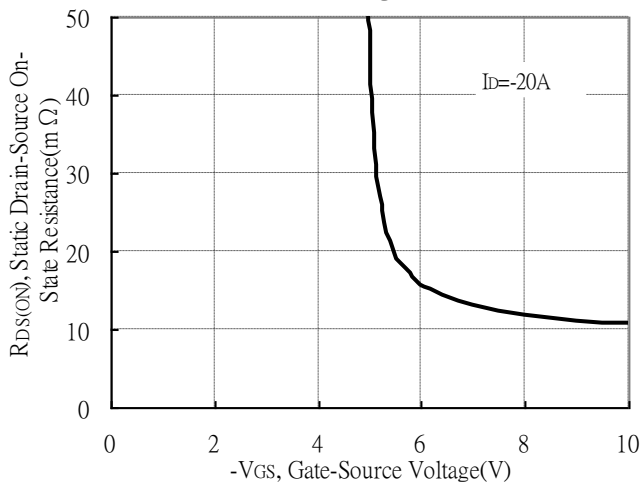
Static Drain-Source On-State resistance vs Drain Current



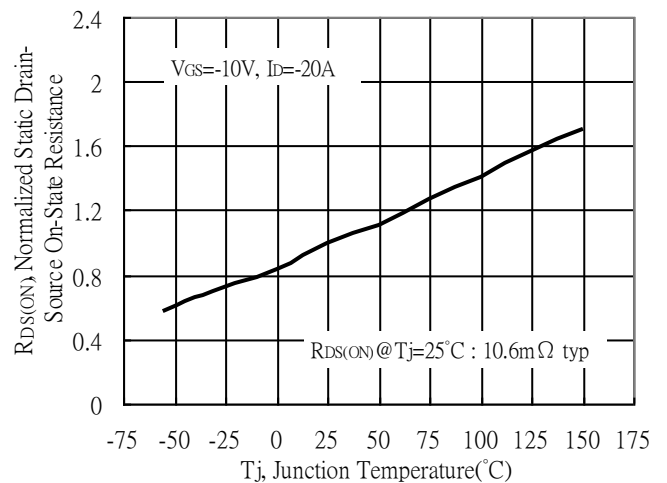
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

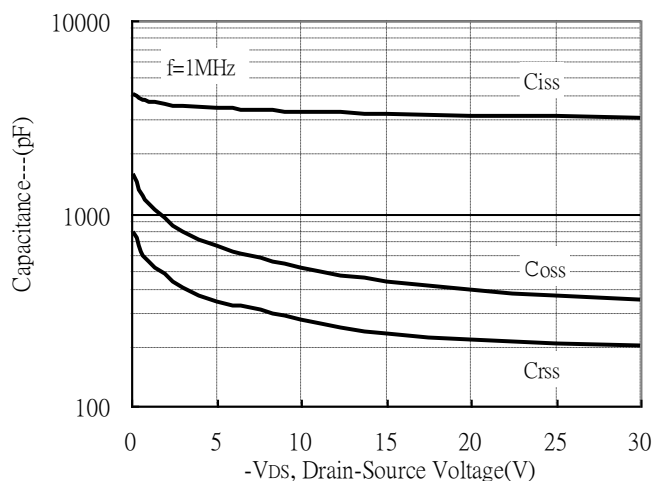


Drain-Source On-State Resistance vs Junction Temperature

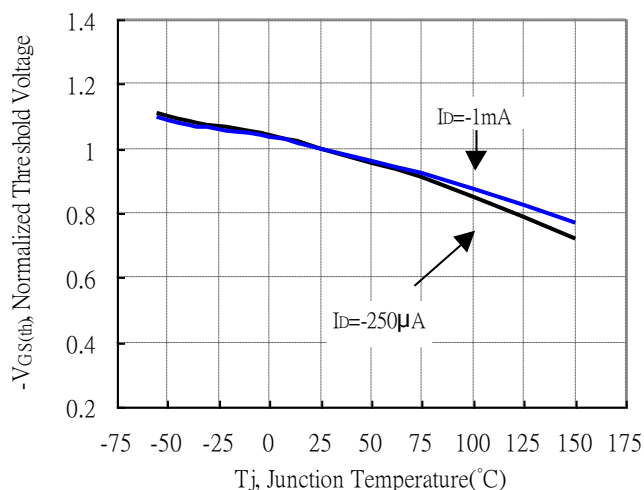


Typical Characteristics(Cont.)

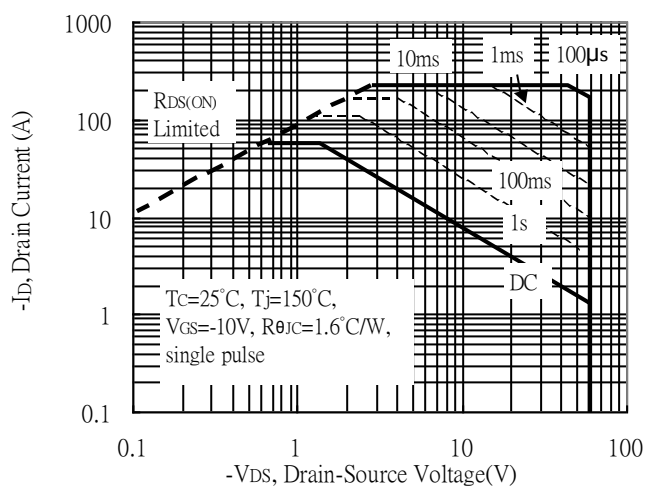
Capacitance vs Drain-to-Source Voltage



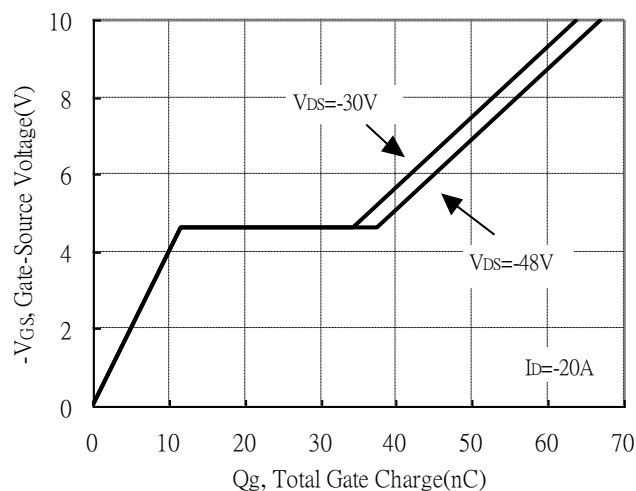
Threshold Voltage vs Junction Temperature



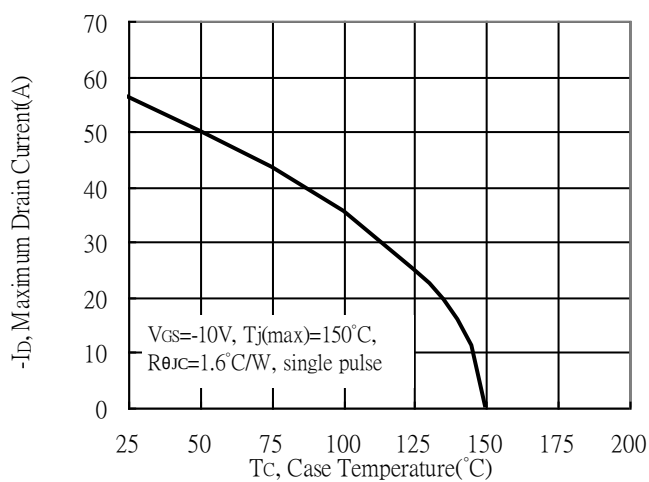
Maximum Safe Operating Area



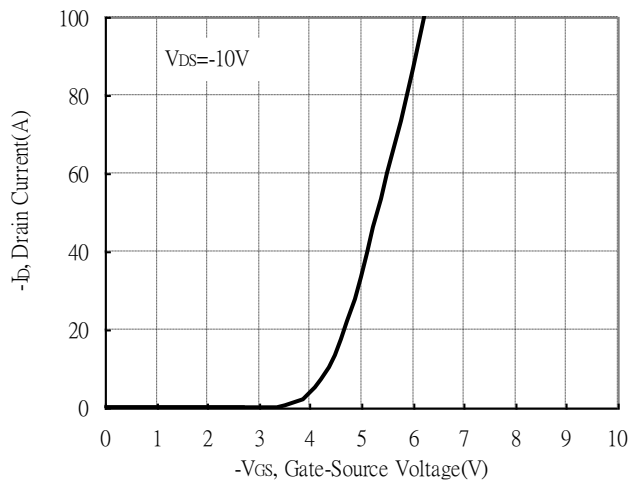
Gate Charge Characteristics



Maximum Drain Current vs Case Temperature

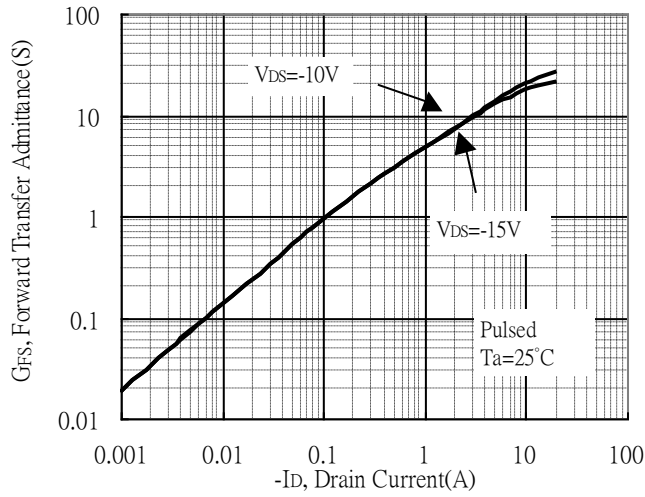


Typical Transfer Characteristics

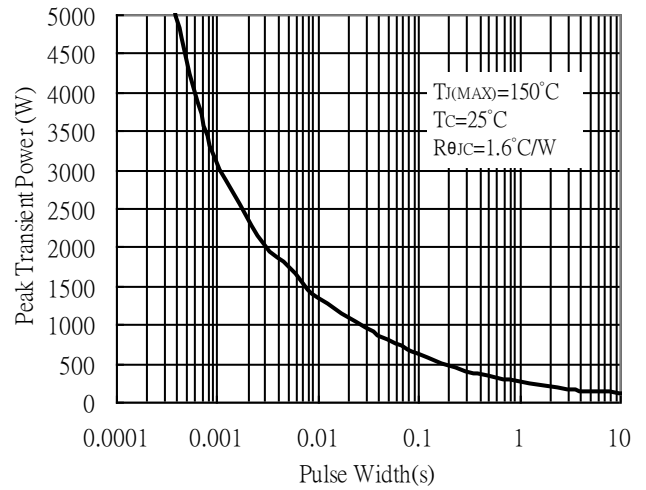


Typical Characteristics(Cont.)

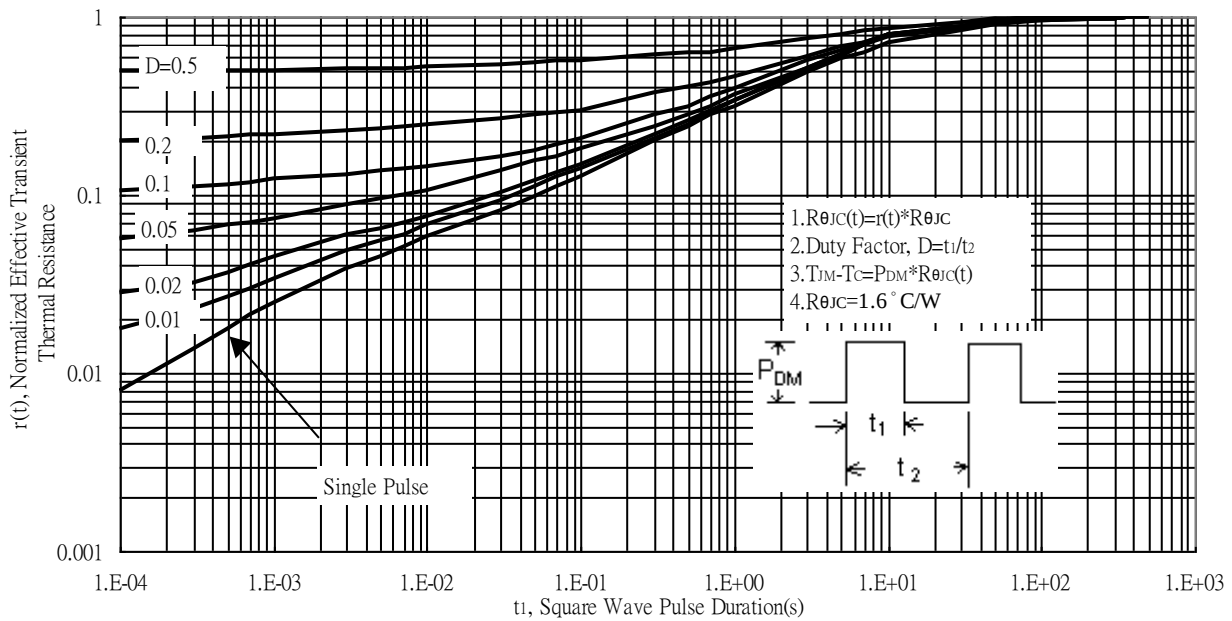
Forward Transfer Admittance vs Drain Current



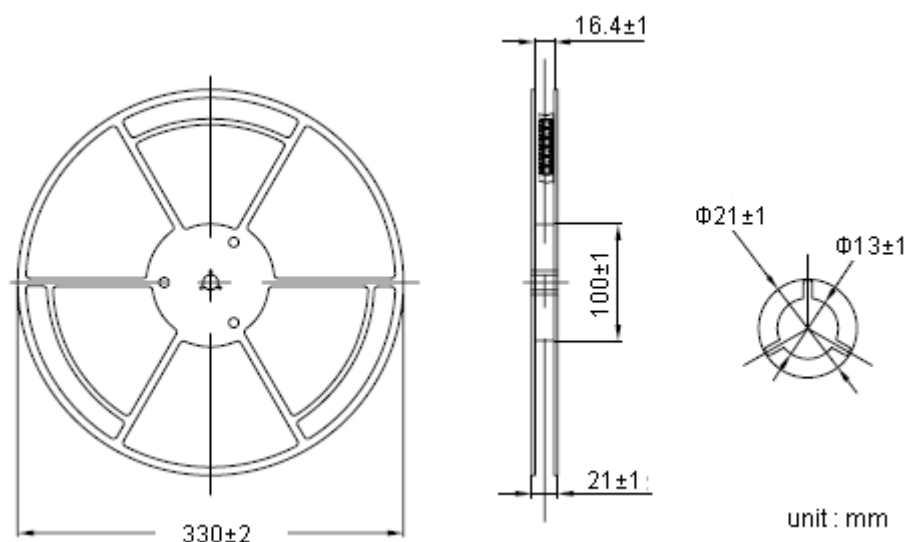
Single Pulse Maximum Power Dissipation



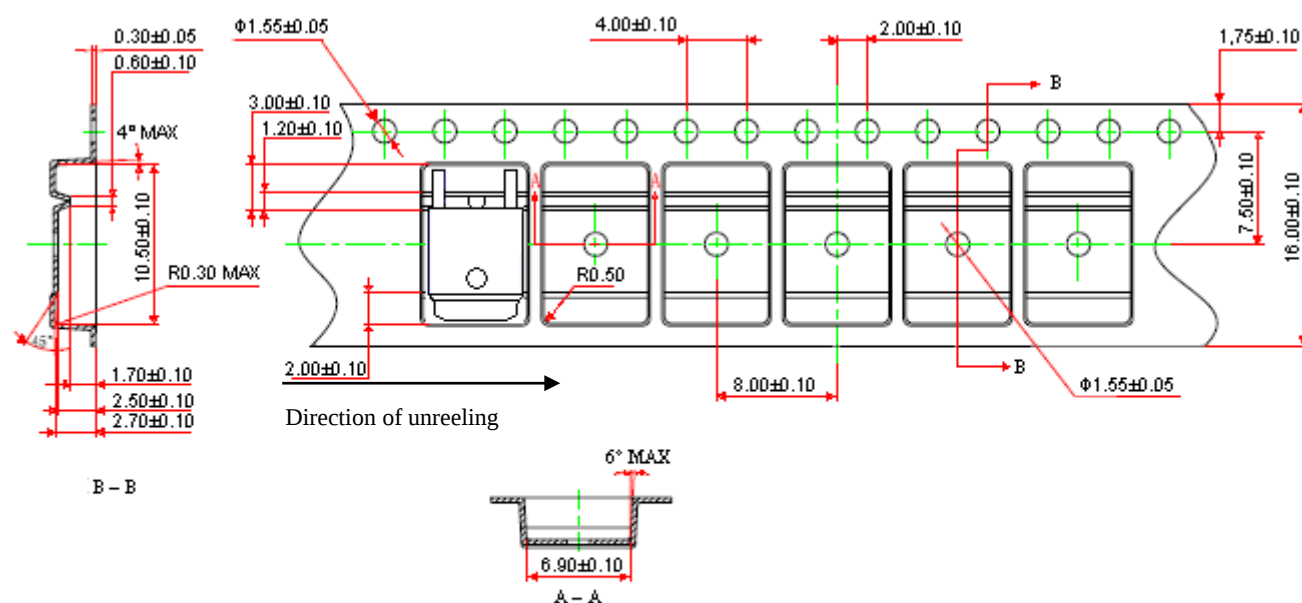
Transient Thermal Response Curves



Reel Dimension



Carrier Tape Dimension

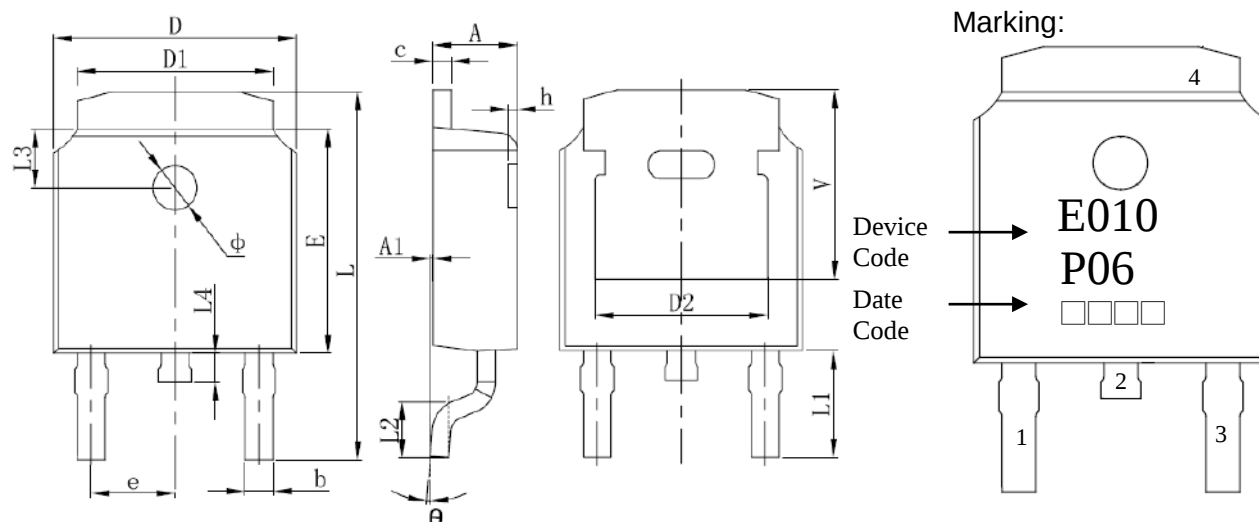


Notes:

- Notes:
1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
 2. Camber not to exceed 1mm in 100mm.
 3. Material: conductive black polystyrene, antistatic coated : $10^5 \Omega/\square \sim 10^{11} \Omega/\square$

unit : mm

TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package

Style: Pin 1.Gate 2.Drain 3.Source
4.Drain

Date Code :

First Code : Last digit of Christian Year

Second Code : Month Code : Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G,
Aug→H, Sep→J, Oct→K, Nov→L, Dec→M

Last Two Codes : Production Serial Code, 01~99

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	L	0.382	0.406	9.712	10.312
A1	0.000	0.005	0.000	0.127	L1	0.114	REF	2.900	REF
b	0.025	0.030	0.635	0.770	L2	0.055	0.067	1.400	1.700
c	0.018	0.023	0.460	0.580	L3	0.063	REF	1.600	REF
D	0.256	0.264	6.500	6.700	L4	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	Φ	0.043	0.051	1.100	1.300
D2	0.190	REF	4.830	REF	θ	0°	8°	0°	8°
E	0.236	0.244	6.000	6.200	h	0.000	0.012	0.000	0.300
e	0.086	0.094	2.186	2.386	v	0.207	REF	5.250	REF